

CIR-S2SUMG8002G

DDR2 SO-DIMM 800MHz 2GB

Description

The CIR-S2SUMG8002G is 256M words x 64 bits, 2 ranks DDR2 SDRAM Small Outline Dual In-line Memory Module, mounting 16 pieces of 1GB bits DDR2 SDRAM sealed in FBGA(μ BGA®) package. Read and write operations are performed at the cross points of the CK and the /CK. This high-speed data transfer is realized by the 4 bits prefetch-pipelined architecture. Data strobe (DQS and /DQS) both for read and write are available for high speed and reliable data bus design. By setting extended mode register, the on-chip Delay Locked Loop(DLL) can be set enable or disable. This module provides high density mounting without utilizing surface mount technology. Decoupling capacitors are mounted beside each FBGA(μ BGA) on the module board.

Specifications

Density	2GB
Pin Count	200pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	128M x 8 bit
Data Rate	800 MHz
CAS Latency	6
Voltage	1.8V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

Features

- All of Lead-Free products are compliant for ROHS
- 200-pin,small outline dual in-line memory module(SO-DIMM)
- 1.8V + 0.1V power supply
- Data rate: 800MHz(max)
- 8 Banks
- JEDEC standard 1.8V I/O(SSTL_18-compatible)
- Burst Length: 4,8
- /CAS Latency (CL): 4,5,6
- Double-data-rate architecture: two data transfers per clock cycle
- Differential clock inputs (CK and /CK)
- Four-bit prefetch architecture
- Auto precharge operation for each burst access
- Auto refresh and self refresh modes
- Differential data strobe(DQS,DQS#) option
- DLL to align DQ and DQS transitions with CK
- Programmable Sequential / Interleave Burst Mode
- Bi-directional Differential Data-Strobe (Single-ended data-strobe is an optional feature)
- Posted CAS# additive latency (AL)
- On Die Termination (ODT)
- 64ms,8192-cycle refresh
- Serial presence detect with EEPROM
- Gold edge contacts
- Average Refresh Period
7.8us at 0°C \leq TCASE \leq +85°C,
3.9us at 85°C \leq TCASE \leq +95°C

